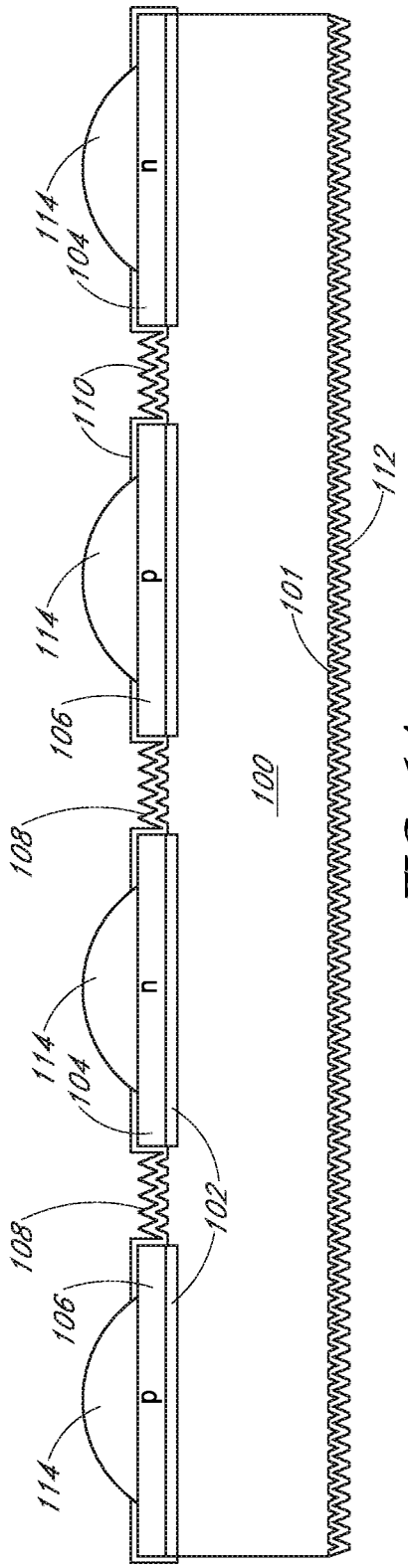


FIG. 1A

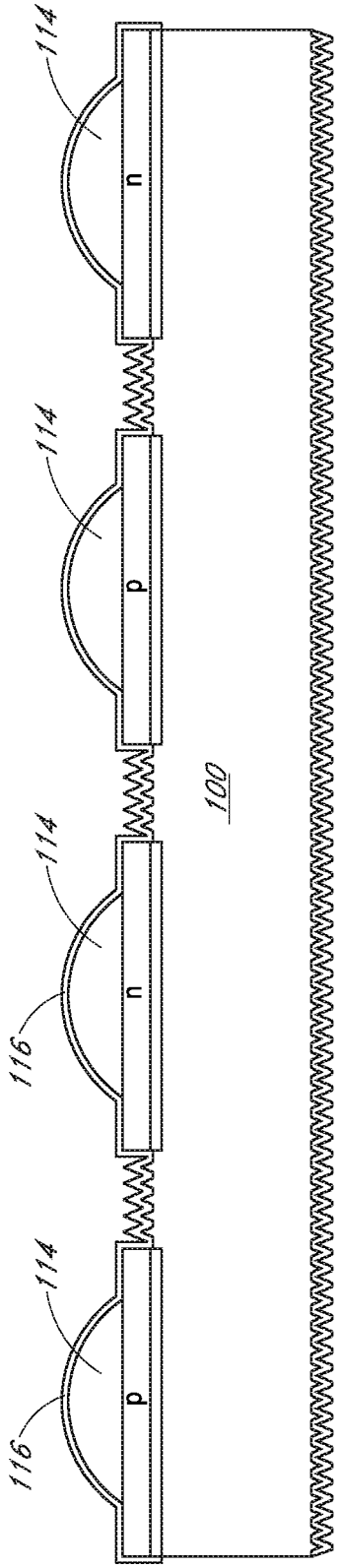


FIG. 1B

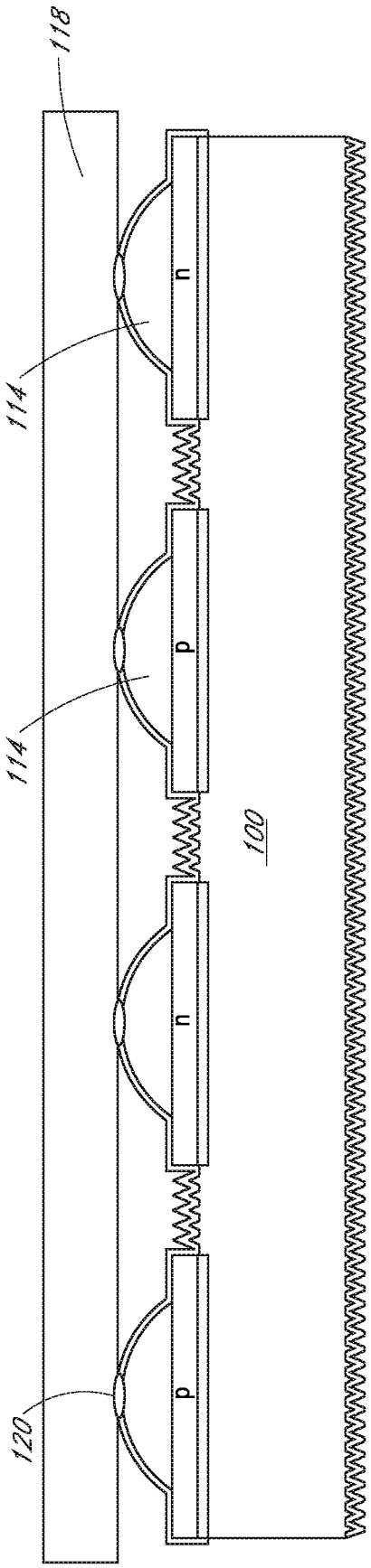


FIG. 1C

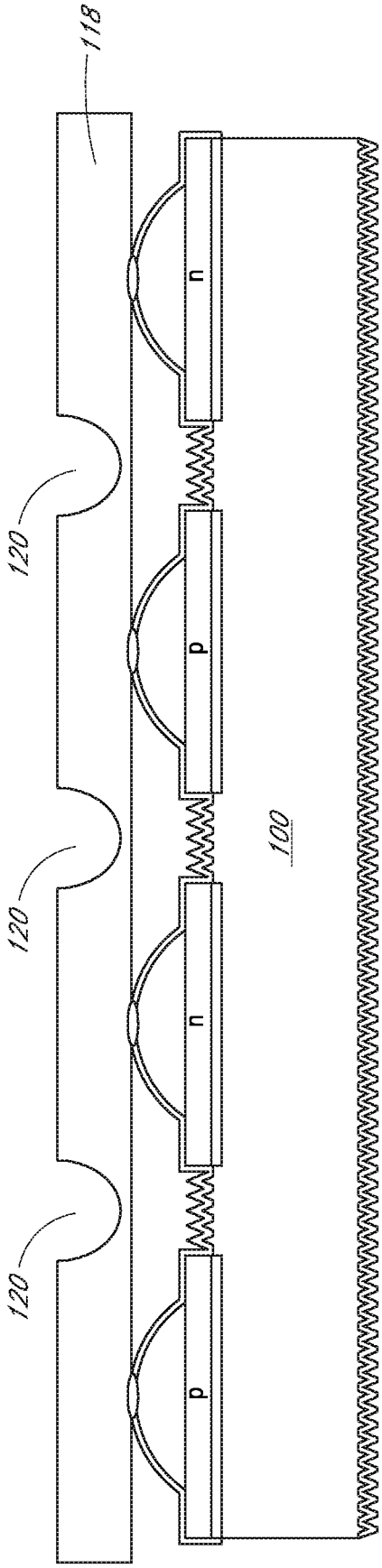


FIG. 1D

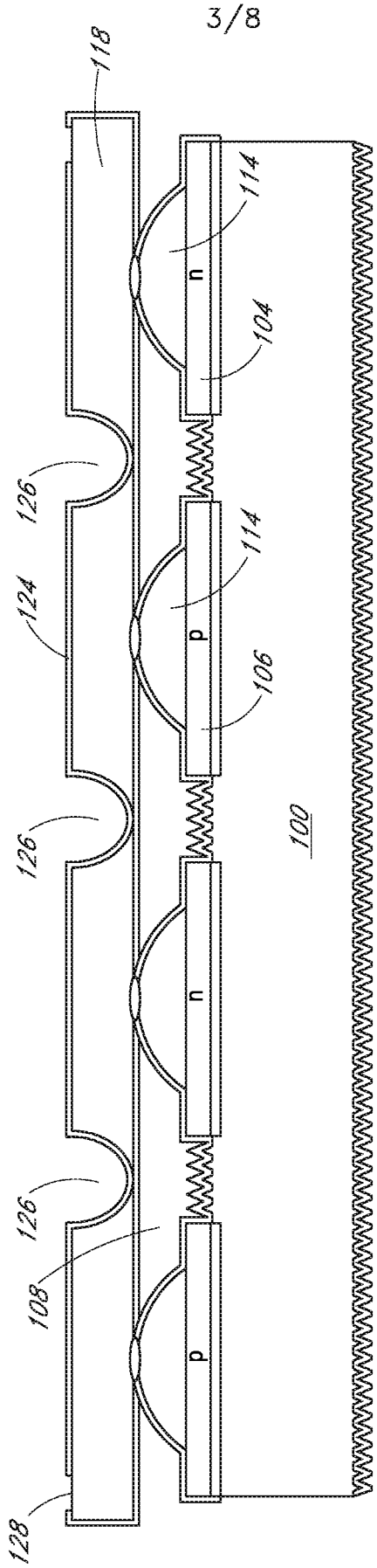


FIG. 1E

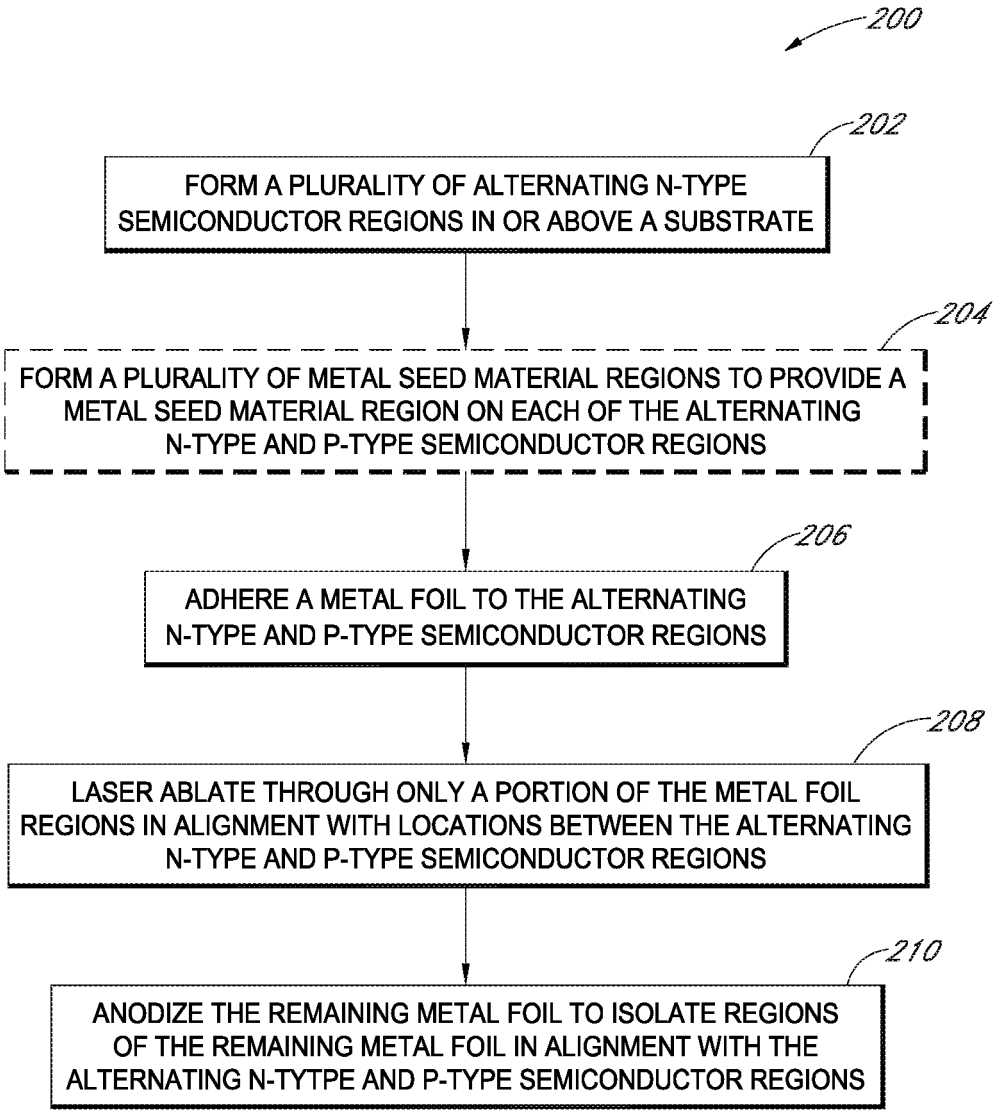

200
202
FORM A PLURALITY OF ALTERNATING N-TYPE SEMICONDUCTOR REGIONS IN OR ABOVE A SUBSTRATE
204
FORM A PLURALITY OF METAL SEED MATERIAL REGIONS TO PROVIDE A METAL SEED MATERIAL REGION ON EACH OF THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS
206
ADHERE A METAL FOIL TO THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS
208
LASER ABLATE THROUGH ONLY A PORTION OF THE METAL FOIL REGIONS IN ALIGNMENT WITH LOCATIONS BETWEEN THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS
210
ANODIZE THE REMAINING METAL FOIL TO ISOLATE REGIONS OF THE REMAINING METAL FOIL IN ALIGNMENT WITH THE ALTERNATING N-TYTPE AND P-TYPE SEMICONDUCTOR REGIONS

FIG. 2

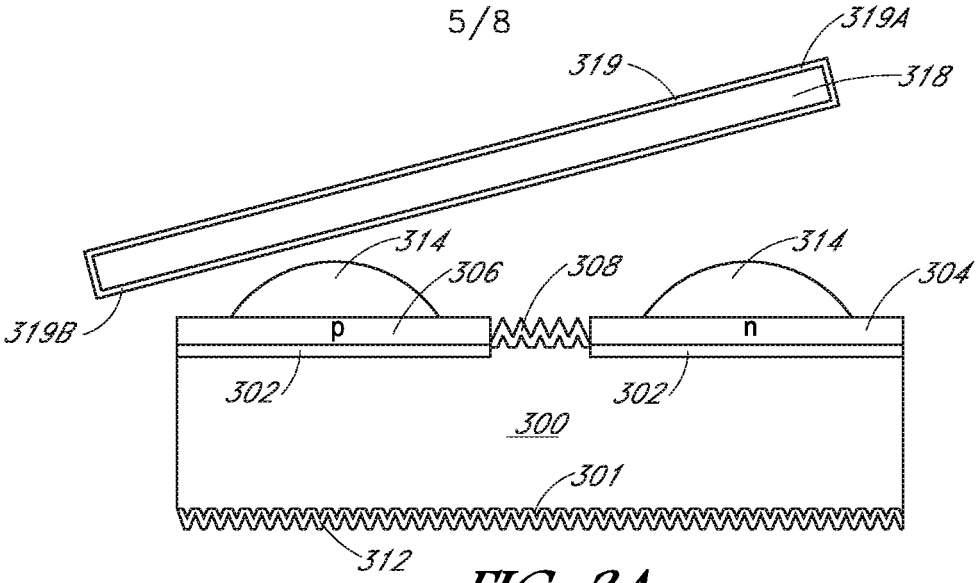


FIG. 3A

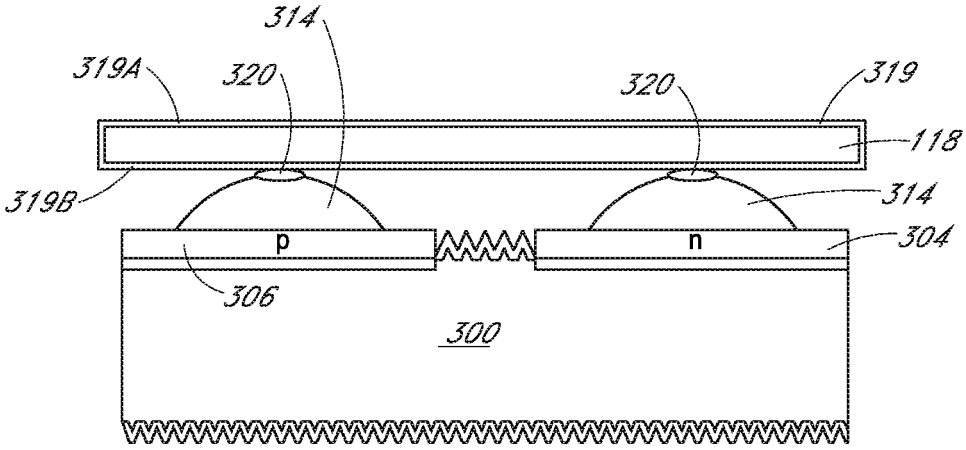


FIG. 3B

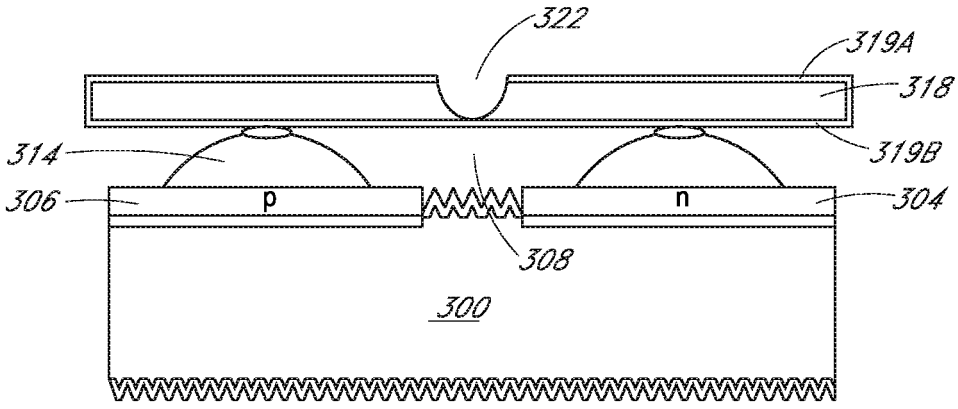


FIG. 3C

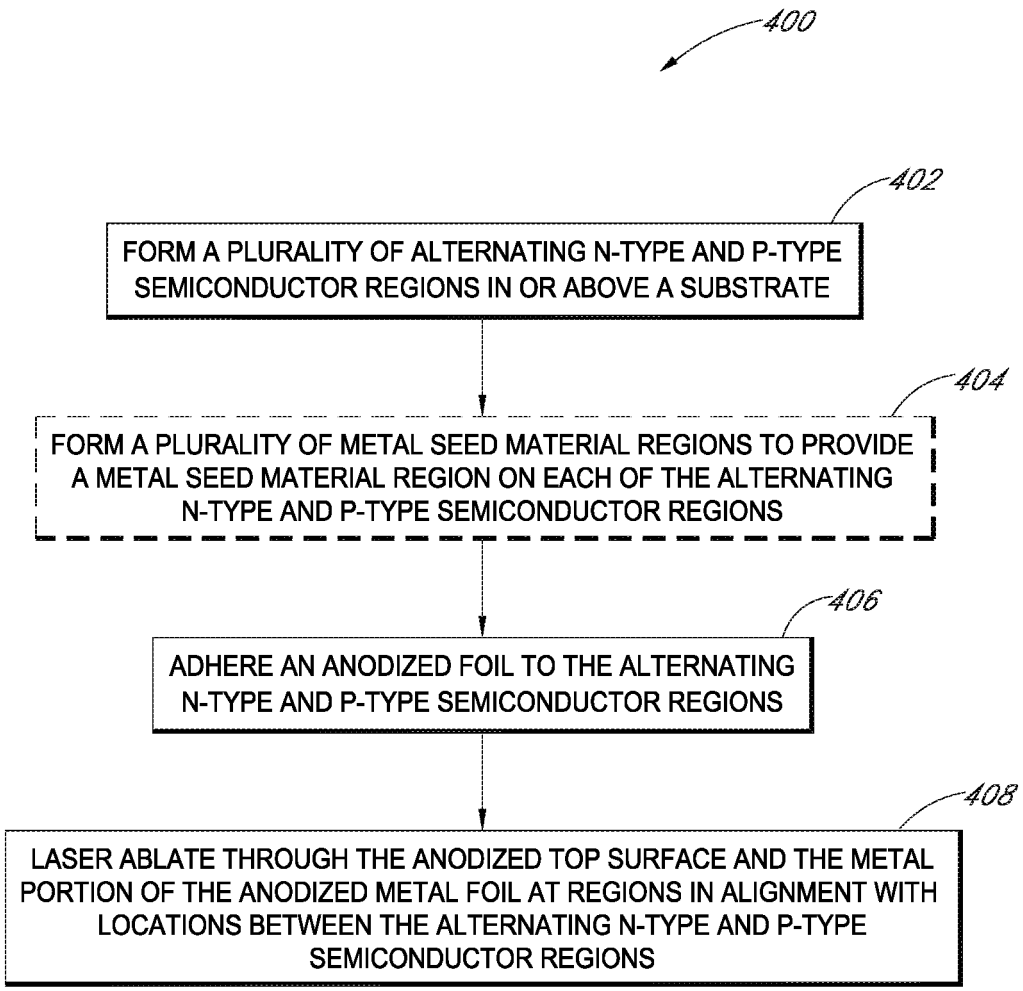

400
402
FORM A PLURALITY OF ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS IN OR ABOVE A SUBSTRATE
404
FORM A PLURALITY OF METAL SEED MATERIAL REGIONS TO PROVIDE A METAL SEED MATERIAL REGION ON EACH OF THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS
406
ADHERE AN ANODIZED FOIL TO THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS
408
LASER ABLATE THROUGH THE ANODIZED TOP SURFACE AND THE METAL PORTION OF THE ANODIZED METAL FOIL AT REGIONS IN ALIGNMENT WITH LOCATIONS BETWEEN THE ALTERNATING N-TYPE AND P-TYPE SEMICONDUCTOR REGIONS

FIG. 4

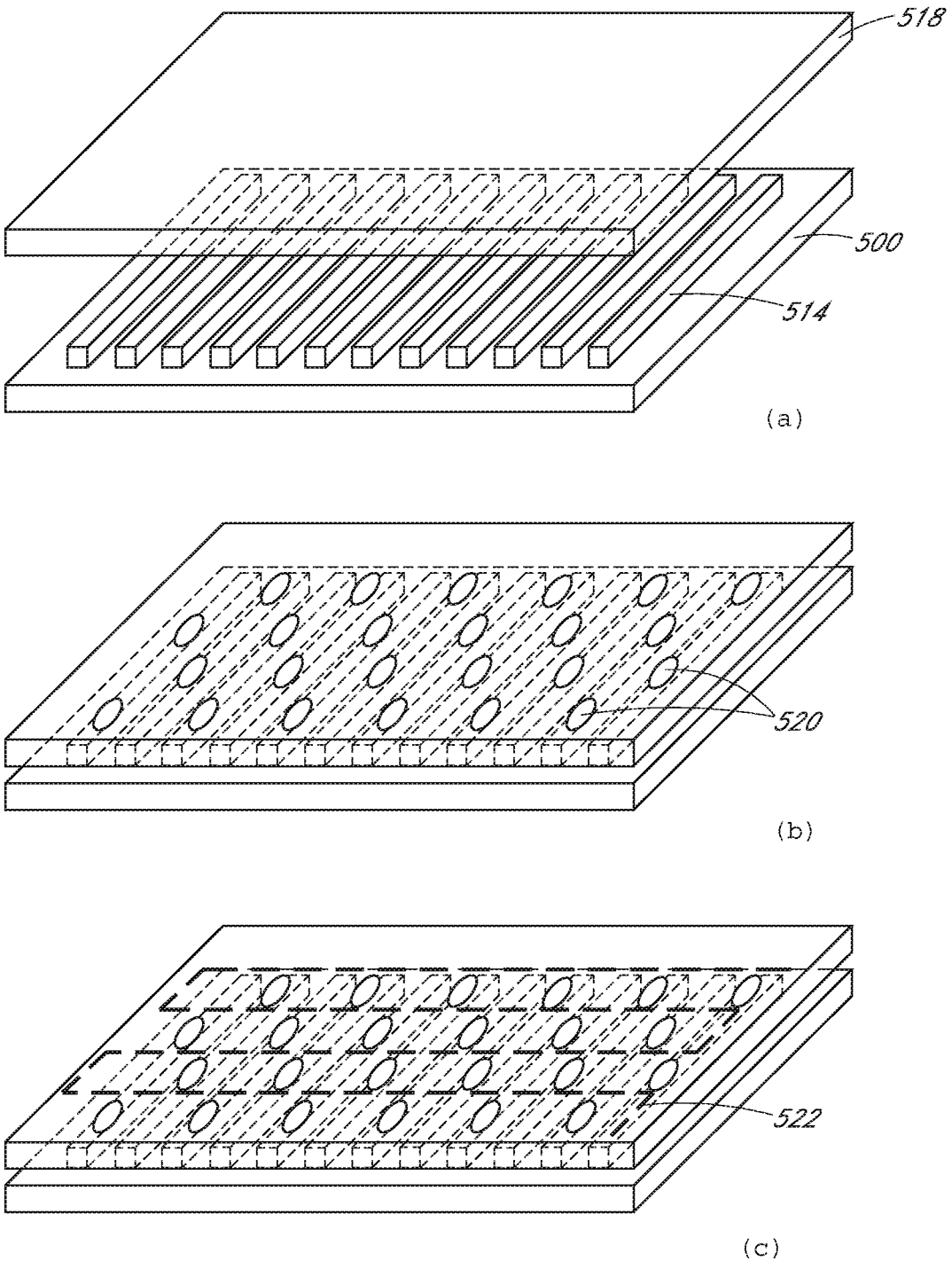


FIG. 5

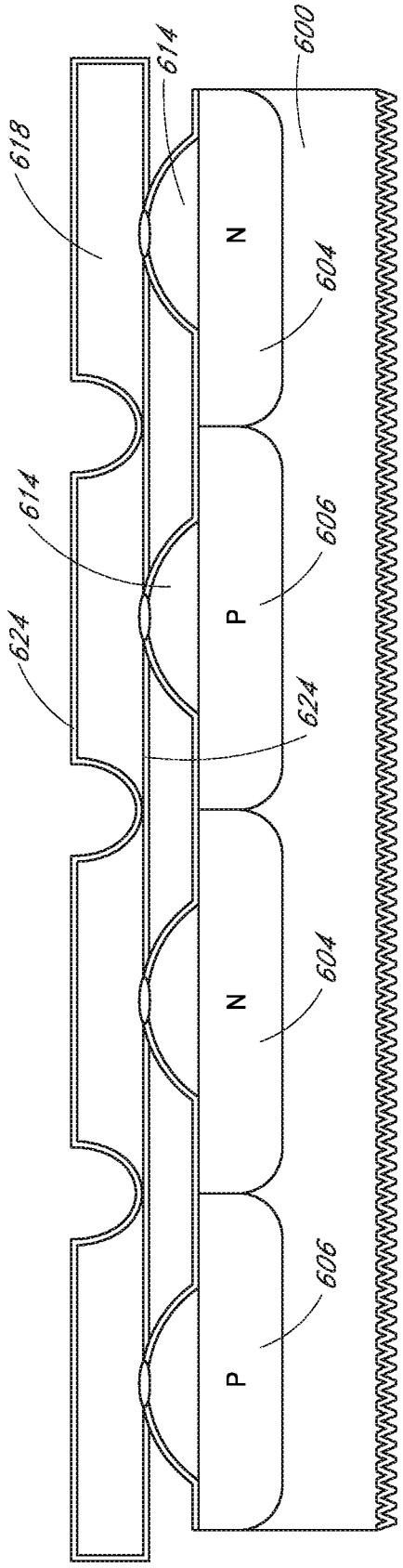

618
614
600
N
604
614
606
P
624
624
N
604
P
606

FIG. 6A

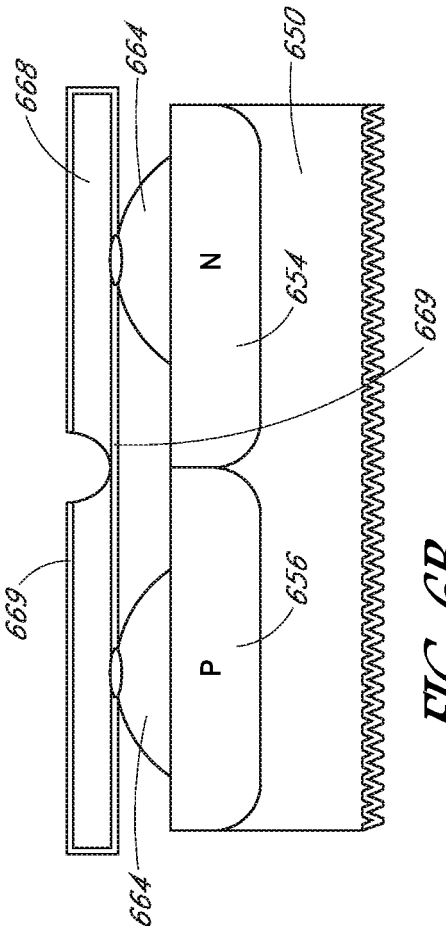

668
664
650
N
654
669
669
P
656
664

FIG. 6B